



### Selection Guide

Part Number	Package
LC5513D	DIP8 with pin 7 removed

The polarity value for current specifies a sink as "+," and a source as "-", referencing the IC.

### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ , unless otherwise specified

Characteristic	Symbol	Notes	Pins	Rating	Unit
Drain Current <sup>1</sup>	$I_{DPeak}$	Single pulse	8 – 1	4.0	A
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	$I_{LPeak} = 2.7\text{ A}$ , $V_{DD} = 99\text{ V}$ , $L = 20\text{ mH}$	8 – 1	86	mJ
Control Part Input Voltage	$V_{CC}$		2 – 1	35	V
OCP Pin Voltage	$V_{OCP}$		3 – 1	-2.0 to 5.0	V
COMP Pin Voltage	$V_{COMP}$		4 – 1	-0.3 to 7.0	V
ISENSE Pin Voltage	$V_{SEN}$		6 – 1	-0.3 to 5.0	V
Allowable Power Dissipation of MOSFET <sup>3</sup>	$P_{D1}$	Mounted on a 15 mm × 15 mm PCB	8 – 1	0.97	W
Operating Ambient Temperature	$T_{OP}$		—	-55 to 125	°C
Storage Temperature	$T_{stg}$		—	-55 to 125	°C
Channel Temperature	$T_{ch}$		—	150	°C

<sup>1</sup>Refer to MOSFET Safe Operating Area Curve.

<sup>2</sup>Refer to MOSFET Avalanche Energy Derating Coefficient Curve.

<sup>3</sup>Refer to MOSFET Temperature versus Power Dissipation Curve.

### ELECTRICAL CHARACTERISTICS of Control Part $T_A = 25^\circ\text{C}$ , $V_{CC} = 20\text{ V}$ , unless otherwise specified

Characteristic	Symbol	Test Conditions	Pins	Min.	Typ.	Max.	Unit
<b>Startup Operation</b>							
Operation Start Voltage	$V_{CC(ON)}$		2 – 1	13.8	15.1	17.3	V
Operation Stop Voltage*	$V_{CC(OFF)}$		2 – 1	8.4	9.4	10.7	V
Operating Current	$I_{CC(ON)}$		2 – 1	–	–	3.7	mA
Startup Circuit Operation Voltage	$V_{STARTUP}$		8 – 1	42	57	72	V
Startup Current	$I_{CC(STARTUP)}$	$V_{CC} = 13\text{ V}$	2 – 1	-5.5	-3.0	-1.0	mA
Startup Current Threshold Biasing Voltage-1*	$V_{CC(BIAS)1}$		2 – 1	9.5	11.0	12.5	V
Startup Current Threshold Biasing Voltage-2	$V_{CC(BIAS)2}$		2 – 1	14.4	16.6	18.8	V
<b>Normal Operation</b>							
PWM Operation Frequency	$f_{OSC}$		8 – 1	11.0	14.0	18.0	kHz
Maximum On-Time	$t_{ON(MAX)}$		8 – 1	30.0	40.0	50.0	$\mu\text{s}$
COMP Pin Control Voltage Lower Limit	$V_{COMP(MIN)}$		4 – 1	0.55	0.90	1.25	V
Error Amplifier Reference Voltage	$V_{SEN(TH)}$		6 – 1	0.27	0.30	0.33	V
Error Amplifier Source Current	$I_{SEN(SOURCE)}$		4 – 1	-11	-7	-3	$\mu\text{A}$
Error Amplifier Sink Current	$I_{SEN(SINK)}$		4 – 1	3	7	11	$\mu\text{A}$
Leading Edge Blanking Time	$t_{ON(LEB)}$		3 – 1	–	500	–	ns
Quasi-Resonant Operation Threshold Voltage-1	$V_{BD(TH1)}$		3 – 1	0.14	0.24	0.34	V
Quasi-Resonant Operation Threshold Voltage-2	$V_{BD(TH2)}$		3 – 1	0.12	0.17	0.22	V
<b>Protection Operation</b>							
OCP Pin Overcurrent Protection (OCP) Threshold Voltage	$V_{OCP}$		3 – 1	-0.66	-0.60	-0.54	V
OCP Pin Source Current	$I_{OCP}$		3 – 1	-120	-40	-10	$\mu\text{A}$
OCP Pin Overvoltage Protection (OVP) Threshold Voltage	$V_{BD(OVP)}$		3 – 1	2.2	2.6	3.0	V
Overload Protection (OLP) Threshold Voltage-1	$V_{COMP(OLP)1}$		4 – 1	5.0	5.5	6.0	V
Overload Protection (OLP) Threshold Voltage-2	$V_{COMP(OLP)2}$		4 – 1	4.1	4.5	4.9	V
ISENSE Pin OVP Threshold Voltage	$V_{SEN(OVP)}$		6 – 1	1.6	2.0	2.4	V
VCC Pin OVP Threshold Voltage	$V_{CC(OVP)}$		2 – 1	28.5	31.5	34.0	V
Thermal Shutdown Activating Temperature	$T_{J(TSD)}$		–	135	–	–	$^\circ\text{C}$

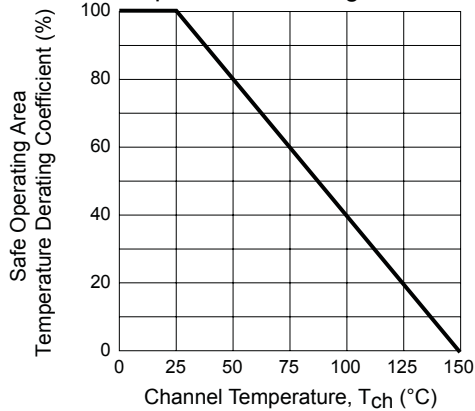
\* $V_{CC(BIAS)1} > V_{CC(OFF)}$  always.

**ELECTRICAL CHARACTERISTICS of MOSFET**  $T_A = 25^\circ\text{C}$ , unless otherwise specified

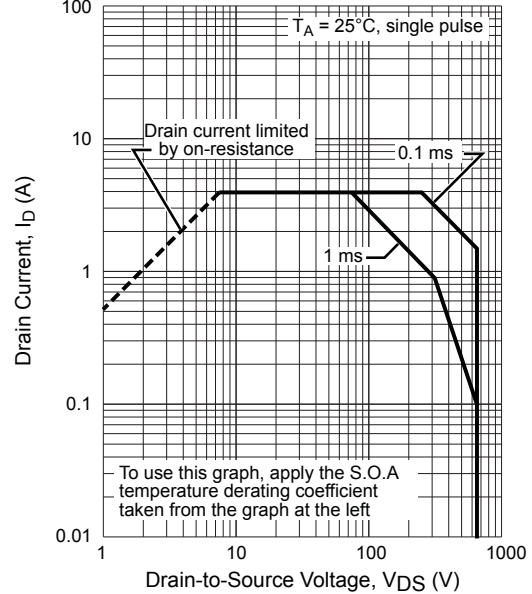
Characteristic	Symbol	Test Conditions	Pins	Min.	Typ.	Max.	Unit
Drain-to-Source Breakdown Voltage	$V_{DSS}$		8 – 1	650	—	—	V
Drain Leakage Current	$I_{DSS}$		8 – 1	—	—	300	$\mu\text{A}$
On Resistance	$R_{DS(on)}$		8 – 1	—	—	1.9	$\Omega$
Switching Time	$t_f$		8 – 1	—	—	400	ns
Thermal Resistance	$R_{\theta ch-c}$	Between channel and case; case temperature, $T_C$ , measured at the center of the case top surface	—	—	—	35.5	$^\circ\text{C/W}$

## Characteristic Performance

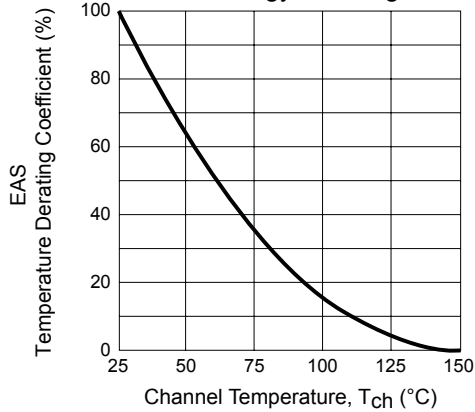
S. O. A. Temperature Derating Coefficient Curve



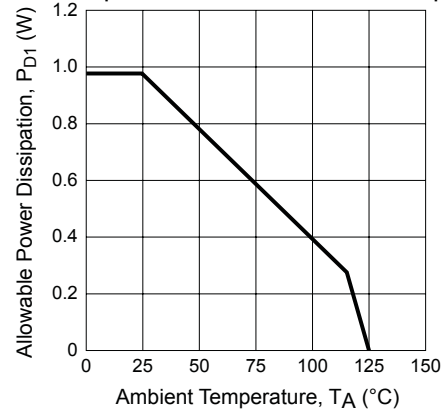
MOSFET Safe Operating Area Curve



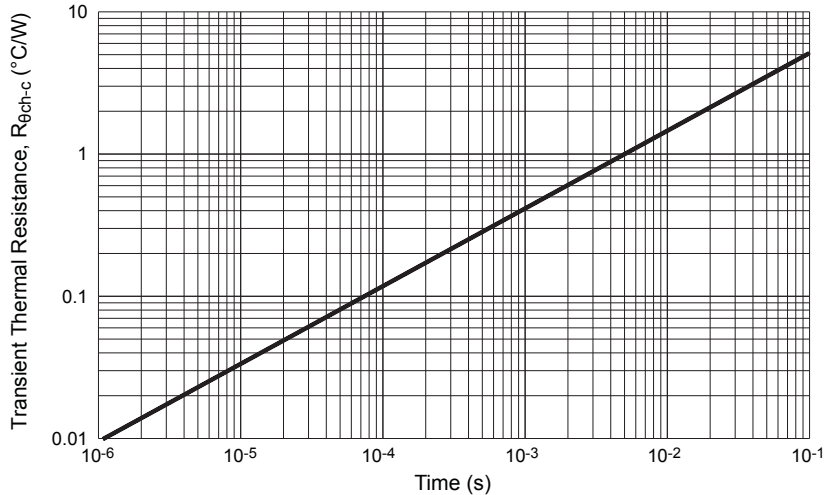
MOSFET Avalanche Energy Derating Coefficient Curve



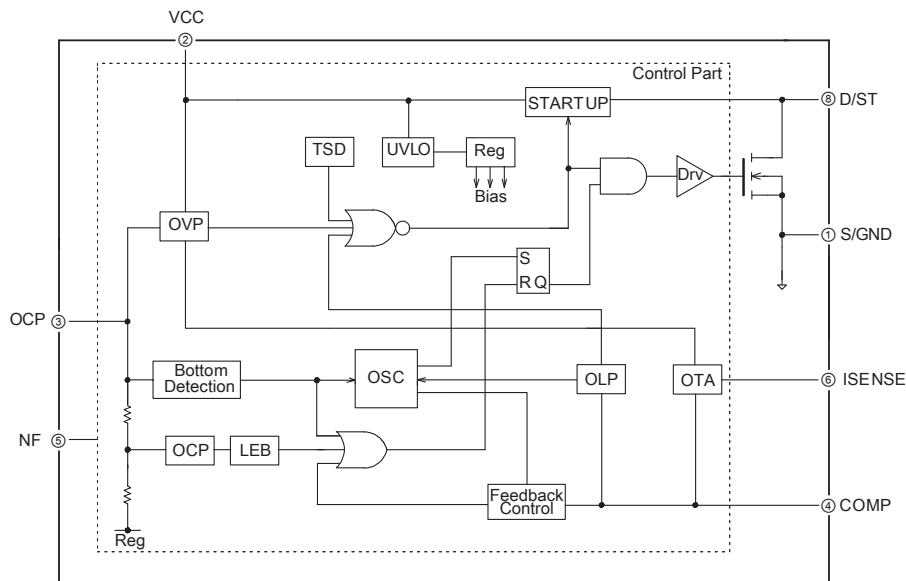
MOSFET Temperature versus Power Dissipation Curve



Transient Thermal Resistance Curve



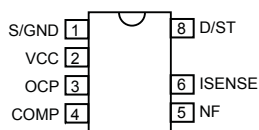
## Functional Block Diagram



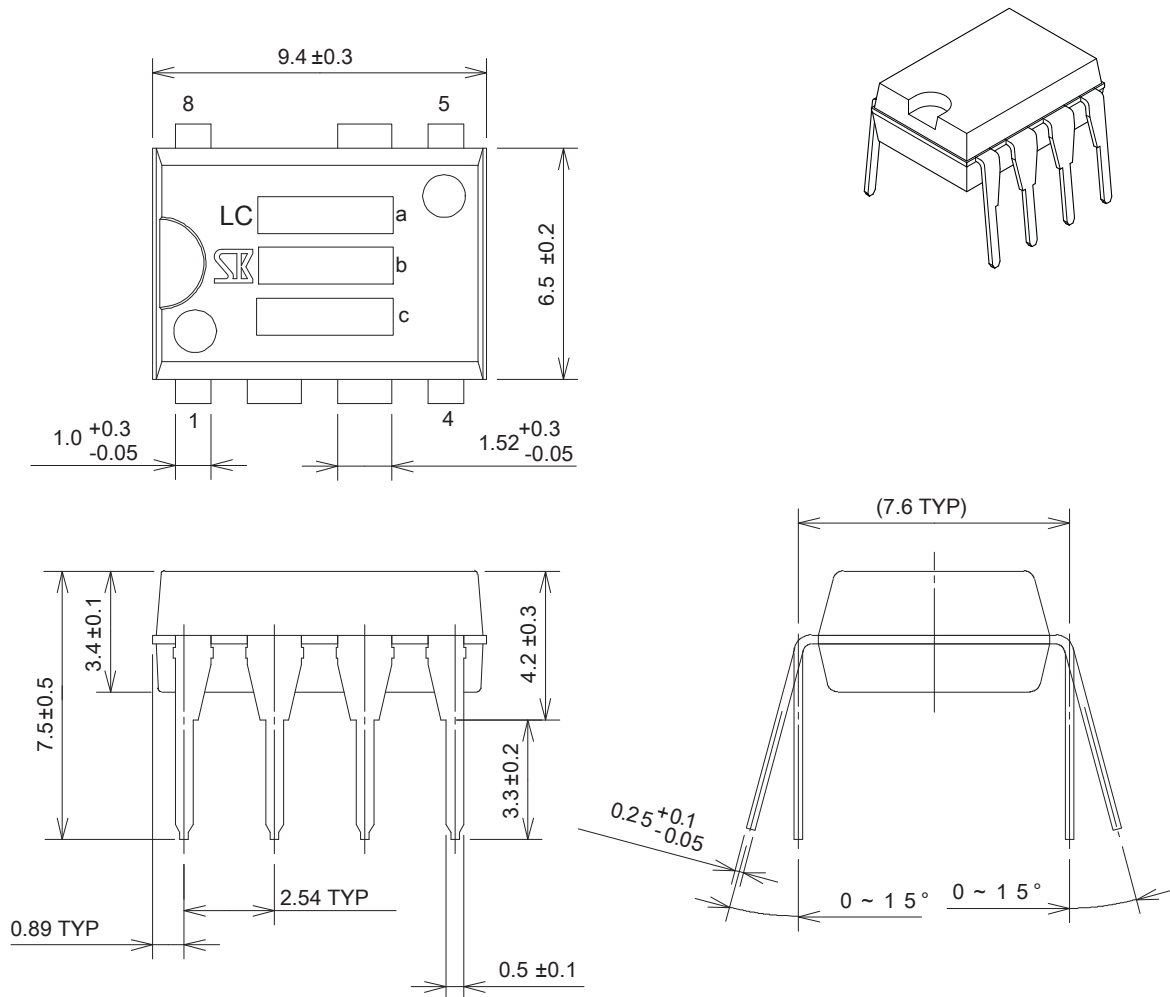
**LC5513D Pin List Table**

Number	Name	Function
1	S/GND	MOSFET source and GND pin for the Control Part
2	VCC	Supply voltage input and Overvoltage protection (OVP) signal input
3	OCP	Overcurrent Protection, quasi-resonant signal input pin, and Overvoltage Protection (OVP) signal input
4	COMP	Feedback phase-compensation input
5	NF	No function; must be externally connected to S/GND pin with as short a trace as possible, for stable operation of the IC
6	ISENSE	Output current detecting voltage input and Overvoltage Protection (OVP) signal input
7	-	Pin removed
8	D/ST	MOSFET drain pin and input of the startup current

### Pin-out Diagram



## Package Outline Drawing, DIP8



Unit: mm

- a: Part #: 5513
- b: Lot number 3 digits, plus D
  - 1<sup>st</sup> letter: Last digit of year
  - 2<sup>nd</sup> letter: Month
    - Jan to September: Numeric
    - October: O
    - November: N
    - December: D
  - 3<sup>rd</sup> letter: Week
    - Date 1 to 10: 1
    - Date 11 to 20: 2
    - Date 21 to 31: 3
- c: Sanken control number



*Pb-free. Device composition compliant  
with the RoHS directive.*

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

### Cautions for Storage

- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40% to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of the products that have been stored for a long time.

### Cautions for Testing and Handling

When tests are carried out during inspection testing and other standard test periods, protect the products from power surges from the testing device, shorts between the product pins, and wrong connections. Ensure all test parameters are within the ratings specified by Sanken for the products.

### Remarks About Using Silicone Grease with a Heatsink

- When silicone grease is used in mounting the products on a heatsink, it shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce excess stress.
- Volatile-type silicone greases may crack after long periods of time, resulting in reduced heat radiation effect. Silicone greases with low consistency (hard grease) may cause cracks in the mold resin when screwing the products to a heatsink.

Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

Type	Suppliers
G746	Shin-Etsu Chemical Co., Ltd.
YG6260	Momentive Performance Materials Inc.
SC102	Dow Corning Toray Co., Ltd.

### Soldering

- When soldering the products, please be sure to minimize the working time, within the following limits:  
260±5°C 10±1 s (Flow, 2 times)  
380±10°C 3.5±0.5 s (Soldering iron, 1 time)
- Soldering should be at a distance of at least 1.5 mm from the body of the products.

### Electrostatic Discharge

- When handling the products, the operator must be grounded. Grounded wrist straps worn should have at least 1 MΩ of resistance from the operator to ground to prevent shock hazard, and it should be placed near the operator.
- Workbenches where the products are handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the products, the head of soldering irons or the solder bath must be grounded in order to prevent leak voltages generated by them from being applied to the products.
- The products should always be stored and transported in Sanken shipping containers or conductive containers, or be wrapped in aluminum foil.



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In addition, it should be noted that since power devices or IC's including power devices have large self-heating value, the degree of derating of junction temperature affects the reliability significantly.

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